



US006369417B1

(12) **United States Patent**
Lee

(10) **Patent No.:** **US 6,369,417 B1**
(45) **Date of Patent:** **Apr. 9, 2002**

(54) **CMOS IMAGE SENSOR AND METHOD FOR FABRICATING THE SAME**

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(*) **Notice:** Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

(21) **Appl. No.:** **09/931,119**

(22) **Filed:** **Aug. 16, 2001**

(30) **Foreign Application Priority Data**

Aug. 18, 2000 (KR) 00-47853

(51) **Int. Cl.⁷** **H01L 31/062; H01L 31/113; H01L 31/0232**

(52) **U.S. Cl.** **257/294; 257/292; 257/432; 438/59; 438/65; 438/69; 438/73**

(58) **Field of Search** **257/290, 291, 257/292, 294, 432; 438/59, 65, 69, 73**

(56) **References Cited**

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(57) **ABSTRACT**

A CMOS image sensor fabrication method that is capable of preventing a surface of a metal line from being damaged or contaminated is provided. The formed CMOS image sensor includes: a semiconductor structure, wherein the semiconductor structure includes a unit pixel area and a pad area; a metal line formed on the pad area, wherein a portion of the metal line is exposed; a passivation layer formed on the unit pixel area and on the metal line such that the exposed portion is left exposed; a planarized photoresist formed on a portion of the passivation layer; a micro-lens formed on a portion of the planarized photoresist; and an oxide layer formed on the entire formed structure such that the exposed portion is left exposed.

15 Claims, 6 Drawing Sheets

